

Am 25. (Amended) A semiconductor device manufactured by the semiconductor device
B
manufacturing method set forth in claim 1.

Respectfully submitted,

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Dated: November 20, 2001

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05988685-112001

12. (Amended) A semiconductor device manufacturing method according to claim 8 [or claim 11], wherein the interlayer insulating film is any one of an FSG film and a porous SiO₂ film.

13. (Amended) A semiconductor device manufacturing method according to claim 6 [or claim 9], wherein the silicon-containing insulating film is any one selected from the group consisting of an SiOCH film, an SiO film, an SiN film, an SiONCH film, an SiCH film, and an SiCNH film.

25. (Amended) A semiconductor device manufactured by the semiconductor device manufacturing method set forth in claim 1 [any one of claims 1, 4, and 9].

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